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November 2013

FDP150N10

N-Channel PowerTrench[®] MOSFET 100 V, 57 A, 15 m Ω

Features

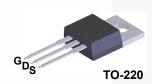
- $R_{DS(on)}$ = 12 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 49 A
- · Fast Switching Speed
- · Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- · High Power and Current Handling Capability
- · RoHS Compliant

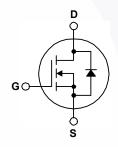
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- · Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- · Motor Drives and Uninterruptible Power Supplies
- · Micor Solar Inverter





MOSFET Maximum Ratings $T_C = 25^{\circ}C$ unless otherwise noted.

| Symbol | | Parameter | | FDP150N10 | Unit | | |
|-----------------------------------|-----------------------------------------|------------------------------------------------------|-------------------|---------------------------------------|------|----|---|
| V_{DSS} | Drain to Source Voltage | Drain to Source Voltage | | | V | | |
| V_{GSS} | Gate to Source Voltage | | | ±20 | V | | |
| | - Continuous (T _C = 25°C) | | | 57 | Α | | |
| ID | Drain Current | Drain Current - Continuous (T _C = 100°C) | | - Continuous (T _C = 100°C) | | 40 | Α |
| I _{DM} | Drain Current | - Pulsed | - Pulsed (Note 1) | | Α | | |
| E _{AS} | Single Pulsed Avalanche Energy (Note 2) | | | 132 | mJ | | |
| dv/dt | Peak Diode Recovery dv | Peak Diode Recovery dv/dt (Note 3) | | 7.5 | V/ns | | |
| D | Power Dissipation | (T _C = 25°C) | | 110 | W | | |
| P_{D} | Power Dissipation | - Derate Above 25°C | | 0.88 | W/°C | | |
| T _J , T _{STG} | Operating and Storage Temperature Range | | | -55 to +150 | °C | | |
| T _L | Maximum Lead Tempera | ature for Soldering, 1/8" from Case fo | or 5 Seconds | 300 | °C | | |

Thermal Characteristics

| Symbol | Parameter FDP150N10 | | | |
|-----------------|----------------------------------------------------|------|------|--|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case, Max. | 1.13 | °C/W | |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient, Max. 62.5 | | C/VV | |

Package Marking and Ordering Information

| Part Number | Top Mark | Package | Packing Method | Reel Size | Tape Width | Quantity |
|-------------|-----------|---------|----------------|-----------|------------|----------|
| FDP150N10 | FDP150N10 | TO-220 | Tube | N/A | N/A | 50 units |

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min. | Тур. | Max. | Unit |
|-----------------------------------------|-------------------------------------------|-----------------------------------------------------------------------------|------|------|------|------|
| Off Charac | eteristics | | | | | |
| BV _{DSS} | Drain to Source Breakdown Voltage | $I_D = 250 \mu A, V_{GS} = 0 V, T_C = 25^{\circ} C$ | 100 | - | - | V |
| ΔBV _{DSS} / ΔT _J | Breakdown Voltage Temperature Coefficient | I _D = 250 μA, Referenced to 25°C | - | 0.1 | - | V/°C |
| 1 | Zero Gate Voltage Drain Current | V _{DS} = 100 V, V _{GS} = 0 V | - | - | 1 | μА |
| IDSS | Zero Gate Voltage Drain Guirent | $V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 150^{\circ}\text{C}$ | - | - | 500 | μΑ |
| I_{GSS} | Gate to Body Leakage Current | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | | - | ±100 | nA |

On Characteristics

| V _{GS(th)} | Gate Threshold Voltage | $V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$ | 2.5 | - | 4.5 | V |
|---------------------|--------------------------------------|-----------------------------------------------|-----|-----|-----|----|
| R _{DS(on)} | Static Drain to Source On Resistance | V _{GS} = 10 V, I _D = 49 A | - | 12 | 15 | mΩ |
| 9 _{FS} | Forward Transconductance | V _{DS} = 20 V, I _D = 49 A | - | 156 | - | S |

Dynamic Characteristics

| C _{iss} | Input Capacitance | V - 25 V V - 0 V | - | 3580 | 4760 | pF |
|------------------|------------------------------|-------------------------------------------------------------|---|------|------|----|
| Coss | Output Capacitance | V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz | - | 340 | 450 | pF |
| C _{rss} | Reverse Transfer Capacitance | 1 11112 | 1 | 140 | 210 | pF |

Switching Characteristics

| $t_{d(on)}$ | Turn-On Delay Time | | | - | 47 | 104 | ns |
|---------------------|-------------------------------|------------------------------------------------|----------|-----|-----|-----|----|
| t _r | Turn-On Rise Time | $V_{DD} = 50 \text{ V}, I_{D} = 49 \text{ A},$ | | - | 164 | 338 | ns |
| t _{d(off)} | Turn-Off Delay Time | $V_{GS} = 10 \text{ V}, R_{G} = 25 \Omega$ | | - | 86 | 182 | ns |
| t _f | Turn-Off Fall Time | | (Note 4) | - | 83 | 176 | ns |
| Q _{g(tot)} | Total Gate Charge at 10V | V _{DS} = 80 V, I _D = 49 A, | | - | 53 | 69 | nC |
| Q _{gs} | Gate to Source Gate Charge | V _{GS} = 10 V | | - | 19 | - | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | | (Note 4) | - / | 15 | - | nC |

Drain-Source Diode Characteristics

| I _S | Maximum Continuous Drain to Source Diode Forward Current | | | - | 57 | Α |
|-----------------|----------------------------------------------------------|------------------------------------------------|---|----|-----|----|
| I _{SM} | Maximum Pulsed Drain to Source Diode Forward Current | | - | - | 228 | Α |
| V_{SD} | Drain to Source Diode Forward Voltage | V _{GS} = 0 V, I _{SD} = 49 A | - | - | 1.3 | V |
| t _{rr} | Reverse Recovery Time | V _{GS} = 0 V, I _{SD} = 49 A, | - | 41 | - | ns |
| Q_{rr} | Reverse Recovery Charge | $dI_F/dt = 100 A/\mu s$ | - | 70 | - | nC |

- 1: Repetitive rating: pulse width limited by maximum junction temperature.
- 2: L = 0.11 mH, I_{AS} = 49 A, V_{DD} = 50 V, R_{G} = 25 Ω , starting T_{J} = 25°C. 3: I_{SD} ≤ 49 A, di/dt ≤ 200 A/ μ s, V_{DD} ≤ BV $_{DSS}$, starting T_{J} = 25°C.
- 4: Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

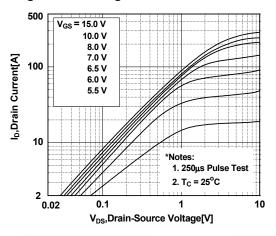


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

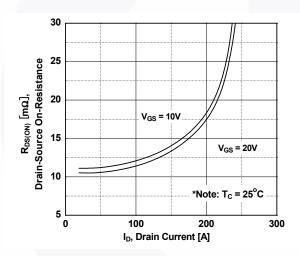


Figure 5. Capacitance Characteristics

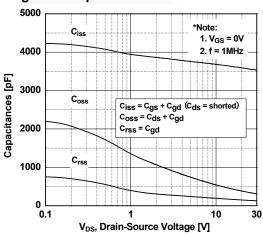


Figure 2. Transfer Characteristics

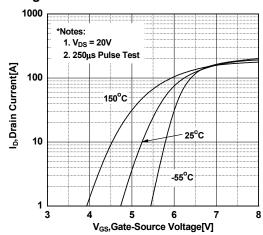


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

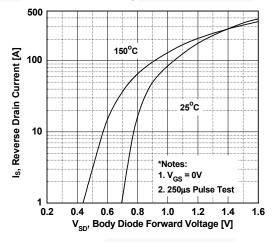
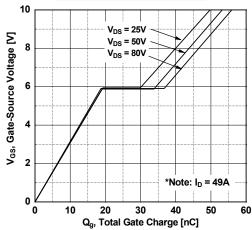


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

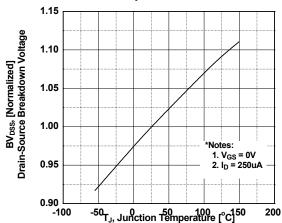


Figure 8. On-Resistance Variation vs. Temperature

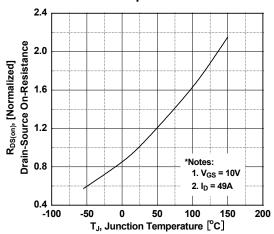


Figure 9. Maximum Safe Operating Area

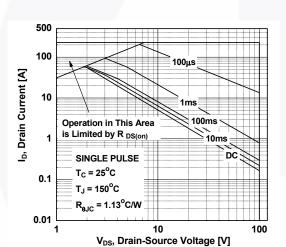


Figure 10. Maximum Drain Current vs. Case Temperature

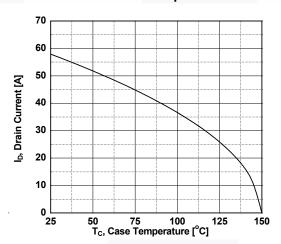
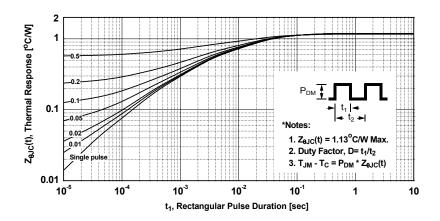


Figure 11. Transient Thermal Response Curve



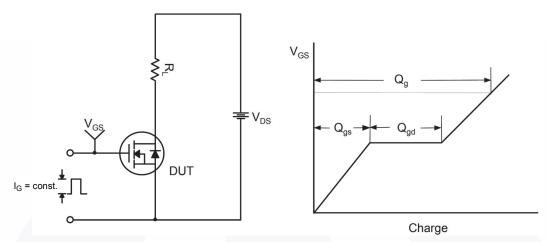


Figure 12. Gate Charge Test Circuit & Waveform



Figure 13. Resistive Switching Test Circuit & Waveforms



Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

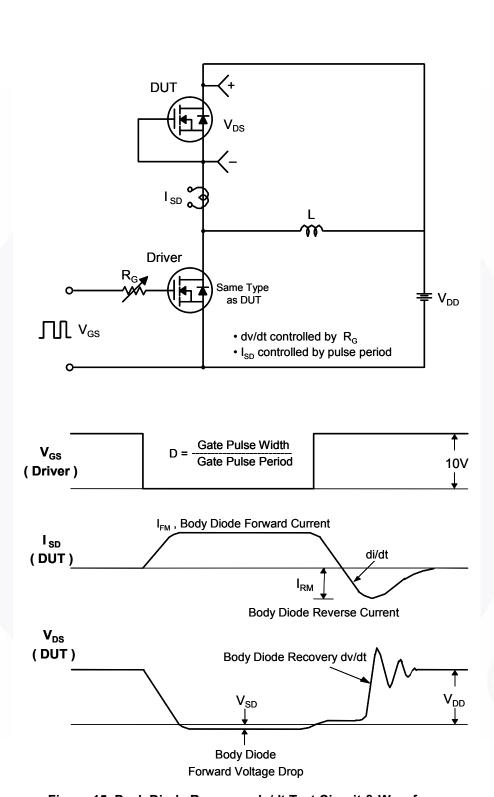


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

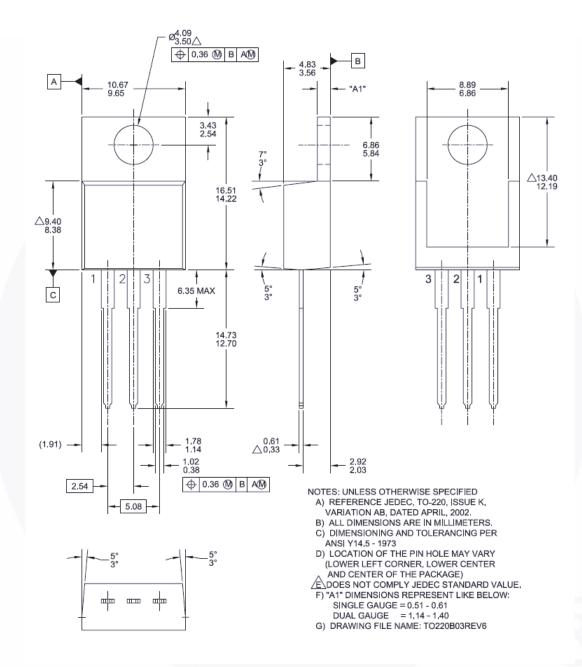


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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